

P-Channel &0-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	- 20				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.034				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -2.5 \text{ V}$	0.046				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -1.8 \text{ V}$	0.067				
I _D (A)	- 5				
Configuration	Single				

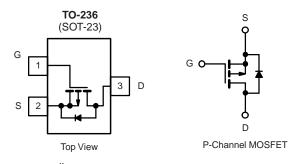
FEATURES

- Halogen-free Option Available
- TrenchFET® Power MOSFET

RoHS COMPLIANT HALOGEN FREE

APPLICATIONS

• Load Switch for Portable Devices



ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	- 20	V	
Gate-Source Voltage		V_{GS}	± 8	V	
Continuous Drain Current	T _C = 25 °C	1	- 5		
	T _C = 125 °C	- I _D	- 3		
Continuous Source Current (Diode Conduction)	I _S	- 2.5	Α		
Pulsed Drain Current ^a	I _{DM}	- 20			
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	- 11		
Single Pulse Avalanche Energy	L=0.1 IIII	E _{AS}	6	mJ	
Maximum Power Dissipation ^a	T _C = 25 °C	D.	2	W	
	T _C = 125 °C	P_{D}	0.67	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient	PCB Mount ^b	R_{thJA}	175	°C/W		
Junction-to-Foot (Drain)	ain)		75	C/VV		

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static						ı	L	
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		- 20	-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$		-	- 1	v	
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$		-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = - 12 V	1	-	- 1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = - 12 V, T _J = 125 °C	-	-	- 50	μΑ	
		$V_{GS} = 0 V$	V _{DS} = - 12 V, T _J = 175 °C	-	-	- 150		
On-State Drain Current ^a	I _{D(on)}	V _{GS} = - 4.5 V	V _{DS} ≤ - 5 V	- 10	-	-	Α	
		V _{GS} = - 4.5 V	I _D = - 3.5 A	-	0.034	-	Ω	
		V _{GS} = - 4.5 V	I _D = - 3.5 A, T _J = 125 °C	-	0.066	-		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V	I _D = - 3.5 A, T _J = 175 °C	-	0.075	-		
		V _{GS} = - 2.5 V	I _D = - 3 A	-	0.046	-		
		V _{GS} = - 1.8 V	I _D = - 2 A	-	0.067	-		
Forward Transconductanceb	9 _{fs}	V _{DS} =	- 5 V, I _D = - 1.6 A	-	7	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}			-	695	870		
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{GS} = 0 V V _{DS} = -6 V, f = 1 MHz		265	335	pF	
Reverse Transfer Capacitance	C _{rss}			-	190	240		
Total Gate Charge ^c	Qg			-	8.4	13		
Gate-Source Charge ^c	Q_{gs}	V _{GS} = - 4.5 V	V _{GS} = - 4.5 V V _{DS} = - 6 V, I _D = - 3.85 A		1	-	nC	
Gate-Drain Charge ^c	Q_{gd}			-	2.4	-		
Gate Resistance	R _g	f = 1 MHz		4.1	8.2	12.3	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	17	26		
Rise Time ^c	t _r	$V_{DD} = -6 \text{ V}, R_L = 1.6 \Omega$ $I_D \cong -3.85 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$		-	19	29	- ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	28	42		
Fall Time ^c	t _f			-	13	20		
Source-Drain Diode Ratings and Chara	acteristics ^b							
Pulsed Current ^a	I _{SM}			=	-	- 20	Α	
Forward Voltage	V _{SD}	I _F = - 2 A, V _{GS} = 0 V		-	- 0.8	- 1.2	V	

Notes

- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

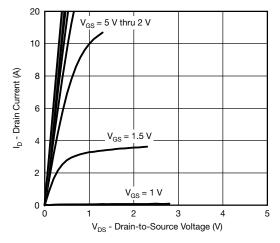
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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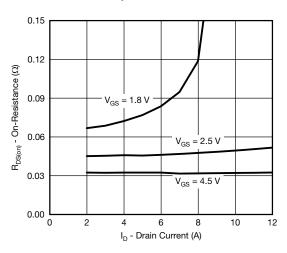
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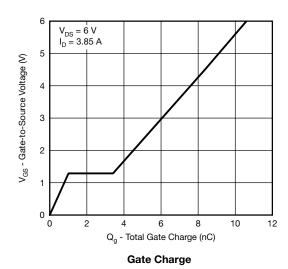
TYPICAL CHARACTERISTICS ($T_A = 25 \, ^{\circ}\text{C}$, unless otherwise noted)

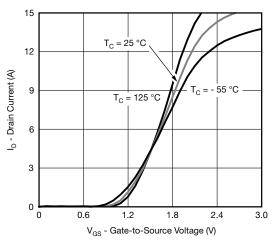


Output Characteristics

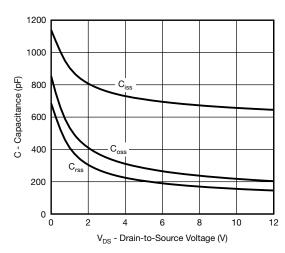


On-Resistance vs. Drain Current

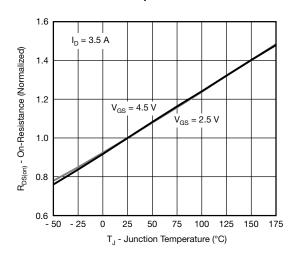




Transfer Characteristics



Capacitance

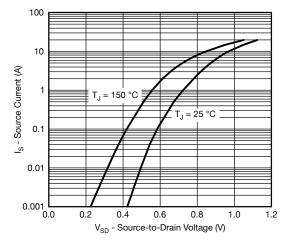


On-Resistance vs. Junction Temperature

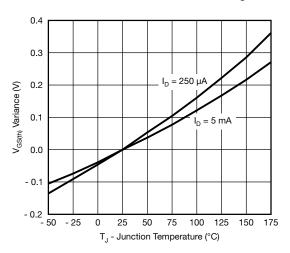
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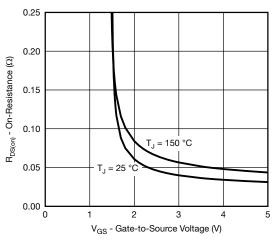
TYPICAL CHARACTERISTICS ($T_A = 25 \, ^{\circ}\text{C}$, unless otherwise noted)



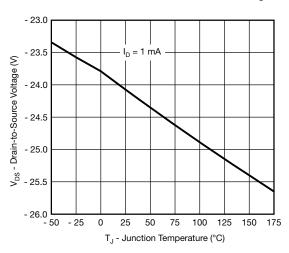
Source-Drain Diode Forward Voltage



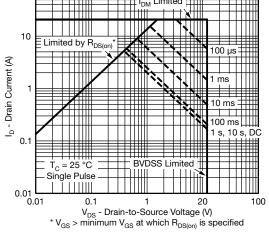
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature

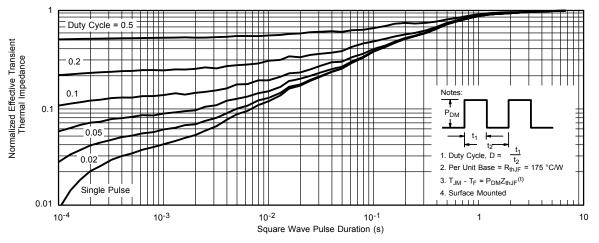


Safe Operating Area

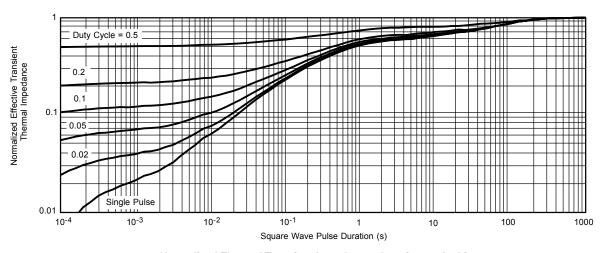
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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot



Normalized Thermal Transient Impedance, Junction-to-Ambient

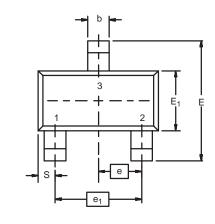
Note

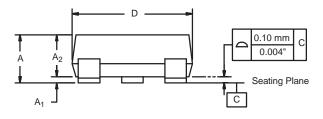
- · The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.



SOT-23 (TO-236): 3-LEAD







Dim -	MILLIM	IETERS	INCHES			
	Min	Max	Min	Max		
Α	0.89	1.12	0.035	0.044		
A ₁	0.01	0.10	0.0004	0.004		
A ₂	0.88	1.02	0.0346	0.040		
b	0.35	0.50	0.014	0.020		
С	0.085	0.18	0.003	0.007		
D	2.80	3.04	0.110	0.120		
E	2.10	2.64	0.083	0.104		
E ₁	1.20	1.40	0.047	0.055		
е	0.95 BSC		0.0374 Ref			
e ₁	1.90	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024		
L ₁	0.64 Ref		0.025 Ref			
S	0.50 Ref		0.020 Ref			
q	3°	8°	3°	8°		
ECN: S-03946-Rev. K. 09-	Jul-01	•				

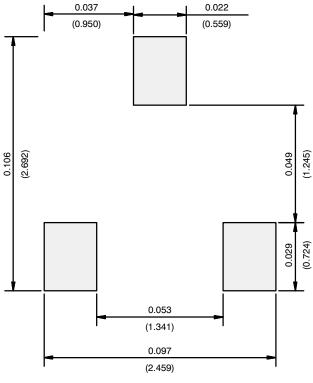
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RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)

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